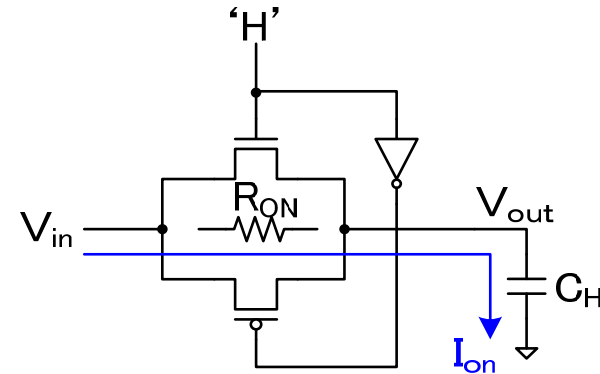
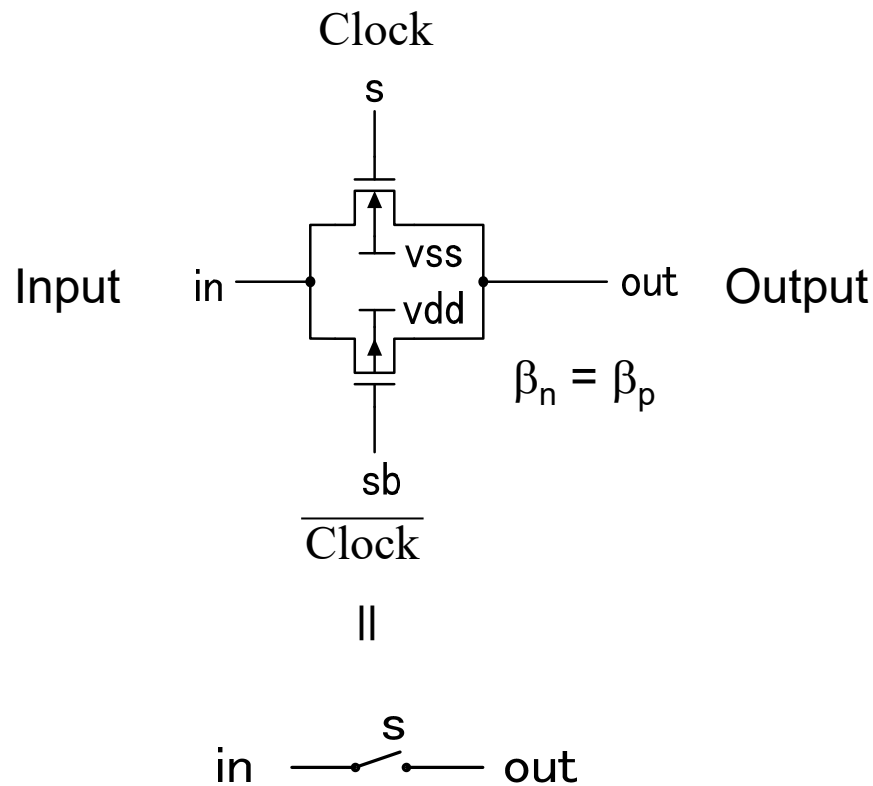


15. Discrete time analog circuits

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Microelectronics Research Lab.
Akio Kitagawa

15.1 Analog switch

Analog switch (CMOS transmission gate)



$$\begin{aligned} \text{Time Constant} &= R_{ON} \cdot C_H \\ &= \frac{C_H}{g_{dsn} + g_{dsp}} \end{aligned}$$

g_{dsn} , g_{dsp} : Channel conductance of n-ch MOSFET and p-ch MOSFET

Conductance of analog switch

There is a minimum conductance at the middle of VDD and VSS.

n-ch MOSFET

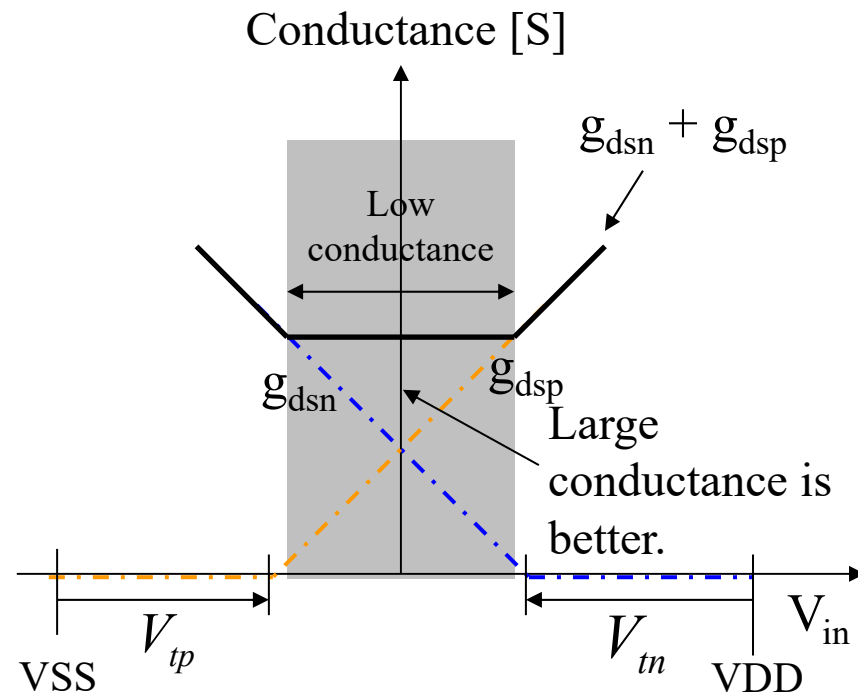
$$\begin{cases} V_{in} - V_{out} = 0 & \text{(Linear region)} \\ V_{gsn} = VDD - V_{in} \\ V_{gsp} = VSS - V_{in} \end{cases}$$

$$\begin{aligned} I_{dsn} &= \beta_n \left\{ (V_{gsn} - V_{Tn}) \cdot V_{dsn} - \frac{1}{2} V_{dsn}^2 \right\} \\ &= \beta_n \left\{ (VDD - V_{in} - V_{Tn}) \cdot V_{in} - \frac{1}{2} V_{in}^2 \right\} \end{aligned}$$

$$g_{dsn} = \frac{1}{r_{dsn}} = \frac{\partial I_{dsn}}{\partial V_{in}} = \beta_n \{ (VDD - V_{Tn}) - 3V_{in} \}$$

p-ch MOSFET

$$g_{dsp} = \frac{1}{r_{dsp}} = \frac{\partial I_{dsp}}{\partial V_{in}} = \beta_p \{ (V_{Tp} - VSS) + 3V_{in} \}$$



Minimum conductance is degraded by the low power supply voltage and high V_{Tn} and V_{Tp} .

ON-resistance of analog switch

Quiz:

Find a ON-resistance of CMOS Switch, assuming that $|V_{Tp}| = V_{Tn} = 0.3(VDD - VSS)$, $\mu_p C_{OX} = 100$ (mA/V²), and $VDD - VSS = 0.5$ (V).

Answer:

Minimum conductance of CMOS switch is observed at $V_{in} = 0$ V, the conductance is minimum, assuming that $\beta_n = \beta_p$.

$$\begin{aligned}g_{dsn} + g_{dsp} &= \beta_n \{(VDD - V_{Tn}) - 3V_{in}\} + \beta_p \{(V_{Tp} - VSS) + 3V_{in}\} \\ &= \beta_p \{(VDD - VSS) - \beta_p \cdot 0.3(VDD - VSS)\} \\ &= 0.7 \beta_p (VDD - VSS) \\ &= 0.35 \beta_p = 35 \frac{W_p}{L_p} \mu S\end{aligned}$$

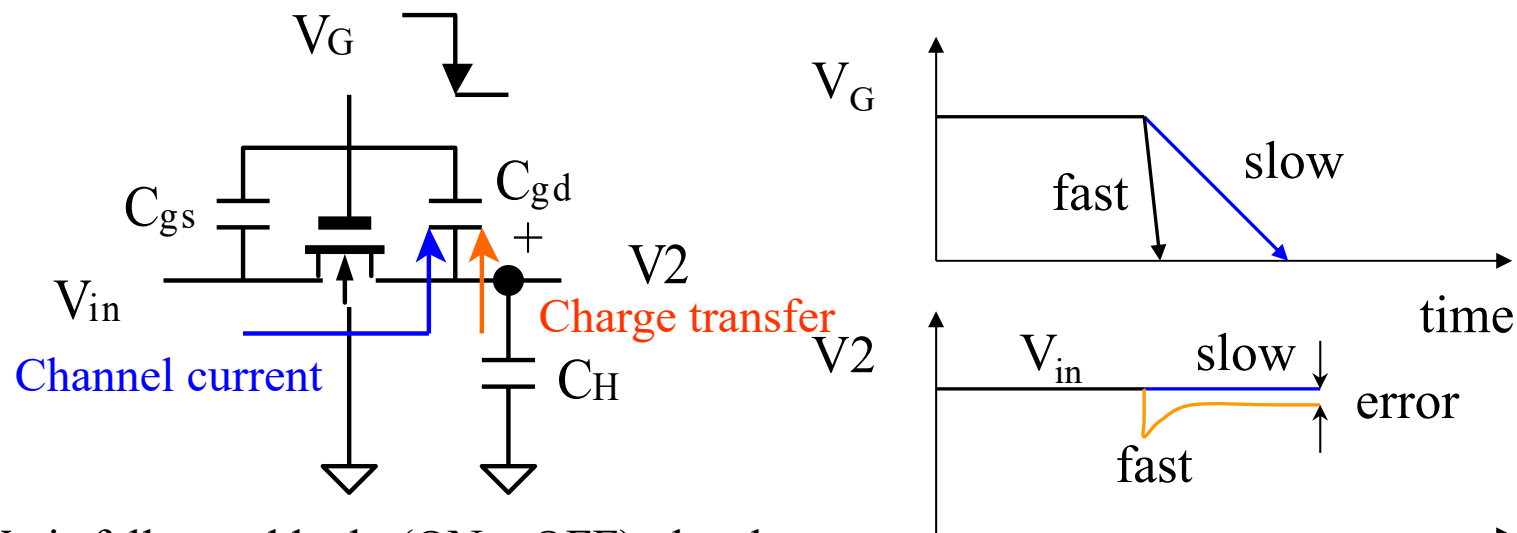
Set W_n and W_p to make V_{in} dependence of the conductance a symmetry for positive and negative voltage.

$$R_{ON} = \frac{1}{g_{dsn} + g_{dsp}} = 29 \frac{L_p}{W_p} \text{ k}\Omega$$

NOTE: Normally, $R_{ON} = \sim 10 \text{ k}\Omega * (L/W)$

Clock feedthrough error

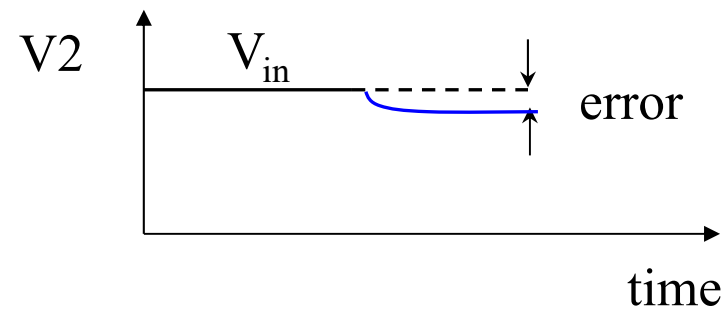
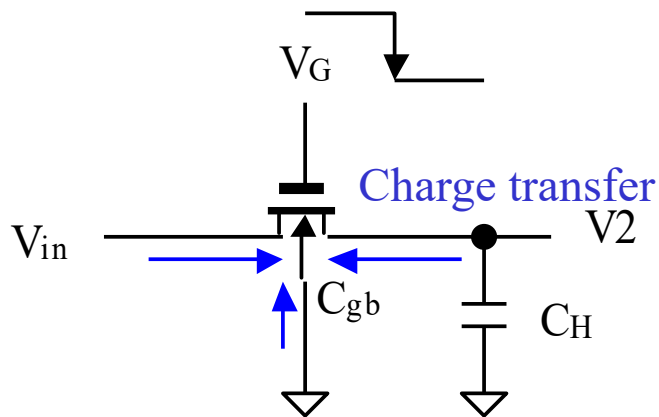
The error is raised by the charge transfer from the sampling capacitor to the parasitic capacitance of MOSFET $\propto L$.



If V_G is fallen suddenly (ON \rightarrow OFF), the charge of C_H is partially transferred to C_{gd} and V_2 is decreased.

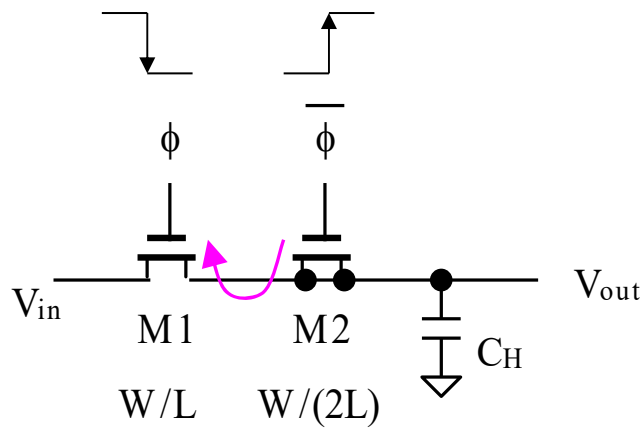
Charge injection error

The error is raised by the charge transfer from the sampling capacitor to the channel of MOSFET $\propto LW$.

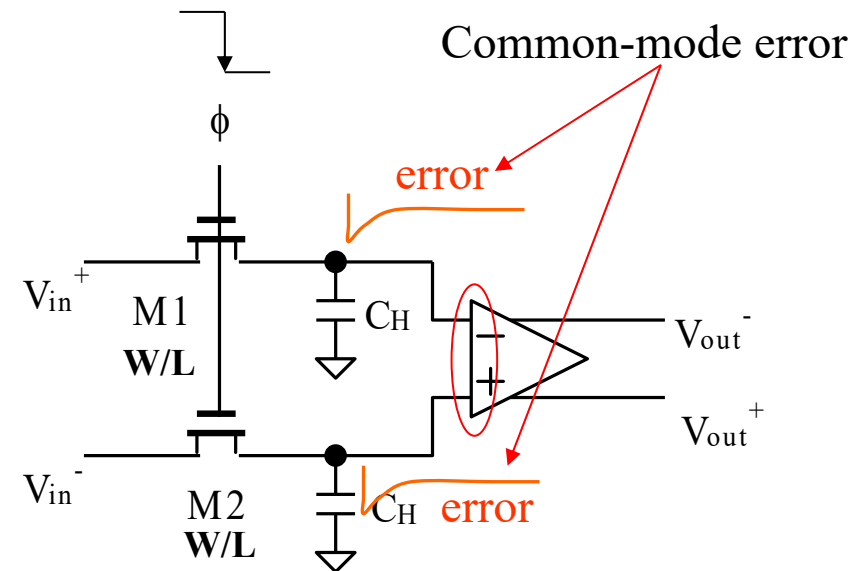


When the carrier in the channel of MOSFET recombine, the charge is injected from C_H and V_2 is decreased.

Cancellation of errors



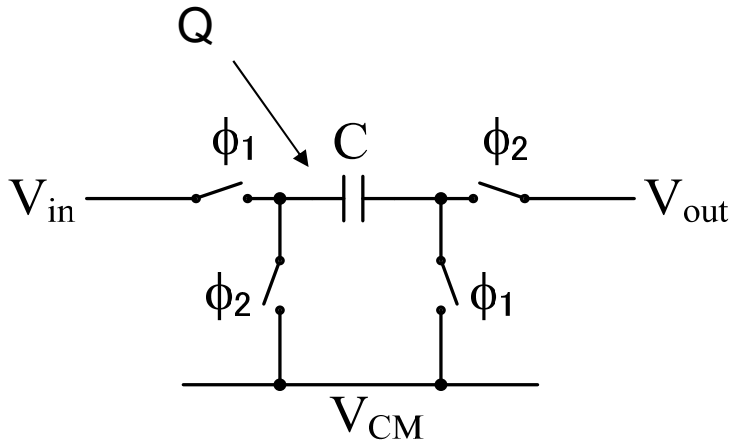
1. Withdraw from a dummy switch



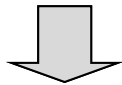
2. Set-off of the common-mode error with the differential amplifier

15.2 Clock circuit

Non-overlapping clock generation

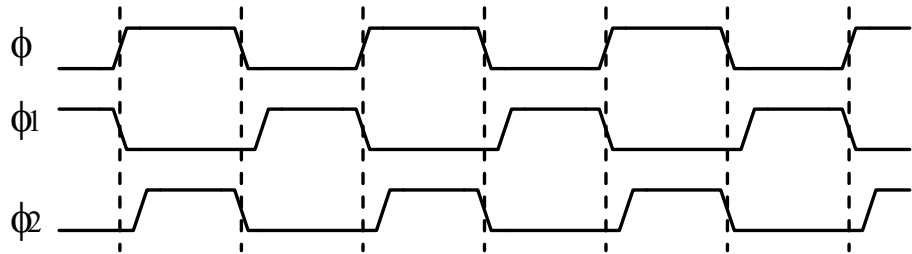
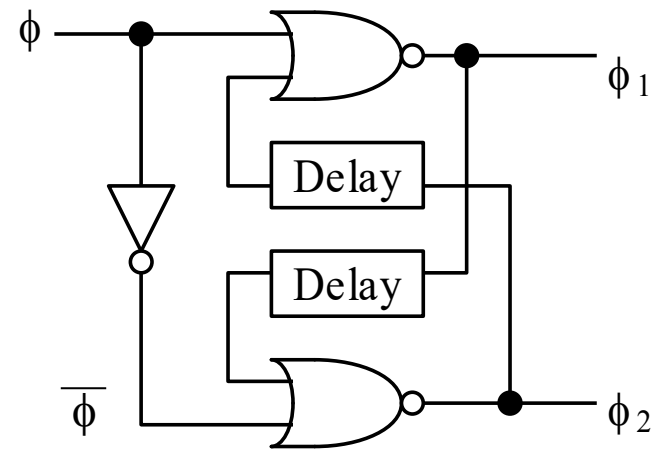


ϕ_1 : $V_{in} = Q/C$ (Sampling of input voltage)
 ϕ_2 : $V_{out} = -Q/C$ (Inversion and output)

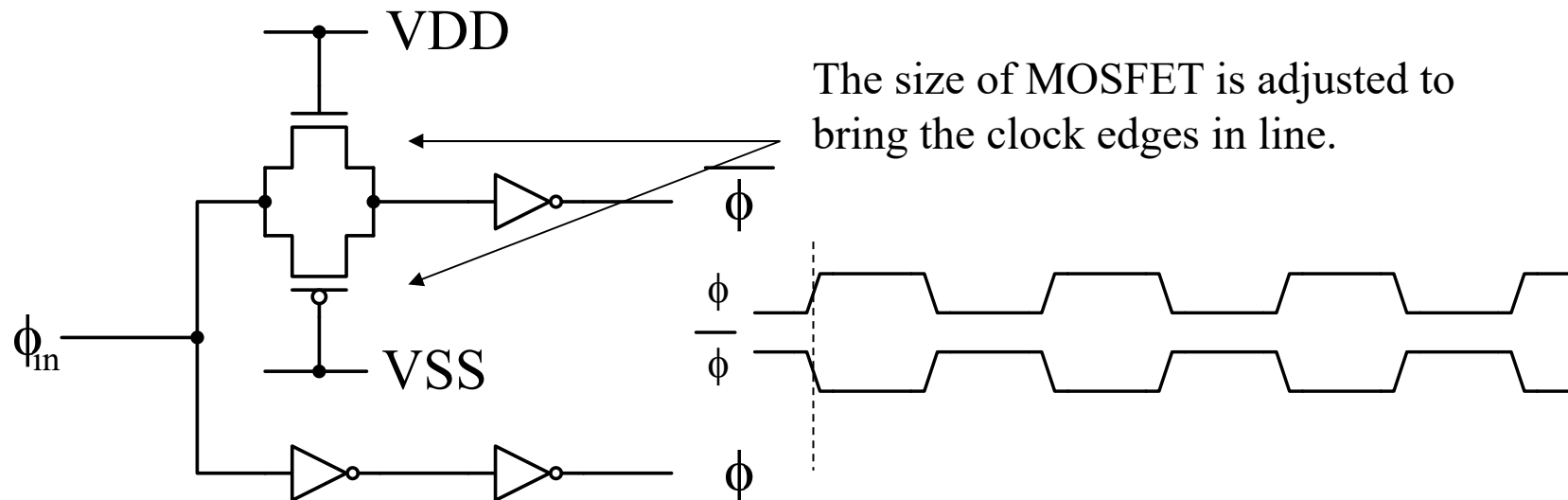


Even if only slightly 'H' level of ϕ_1 and ϕ_2 is overlapped, the sampled charge Q is leaked to V_{CM} line. The non-overlapped clock signals is employed for the ϕ_1 and ϕ_2 .

Non-overlapping Clock Generator

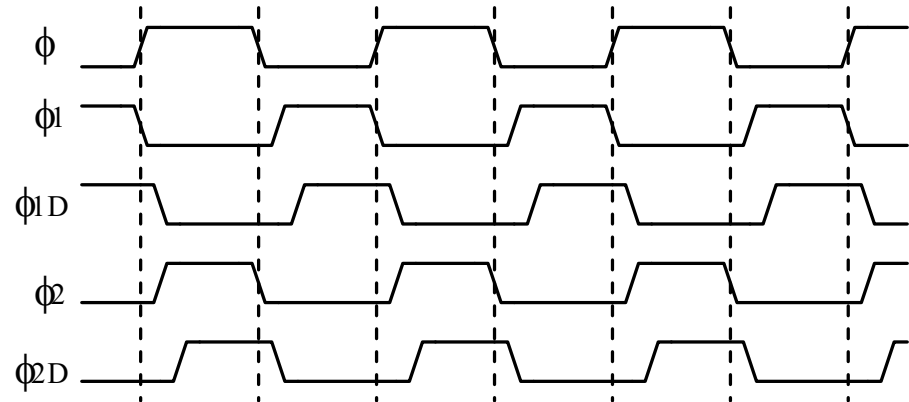
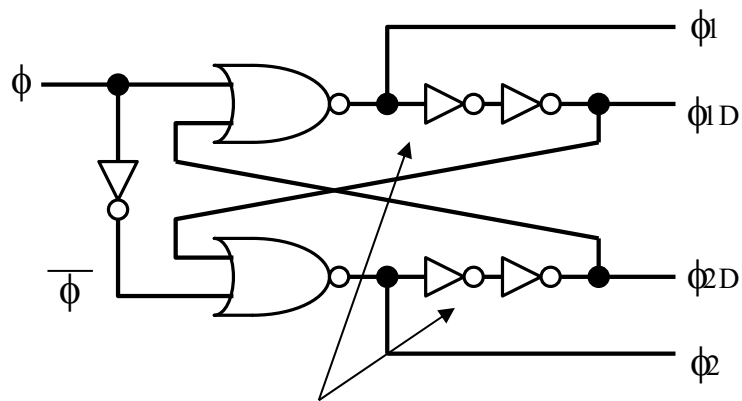
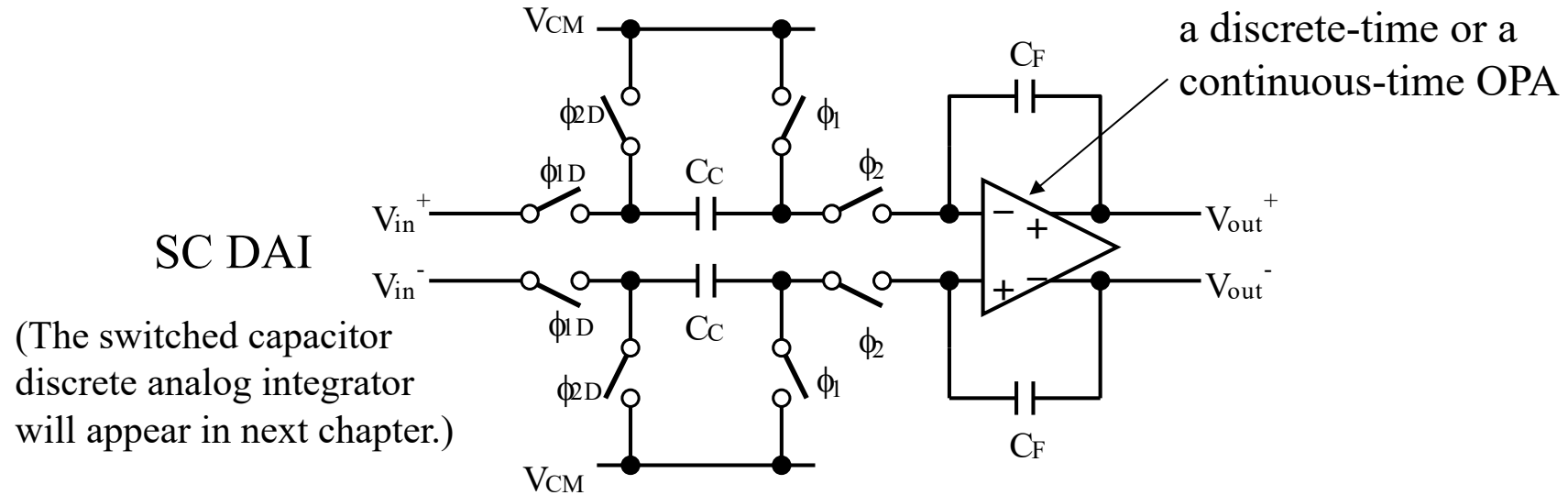


Complementary clock generation



A complementary clock generation circuit is employed to generate the 2-phase clock without a timing error.

Application example of Non-overlapping Clock



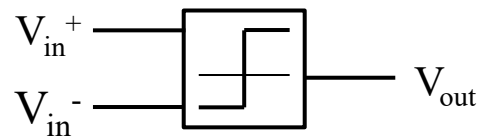
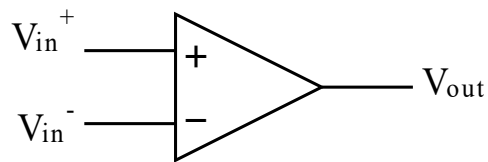
The delay time is adjusted by the number of stages.

15.3 Clocked comparator

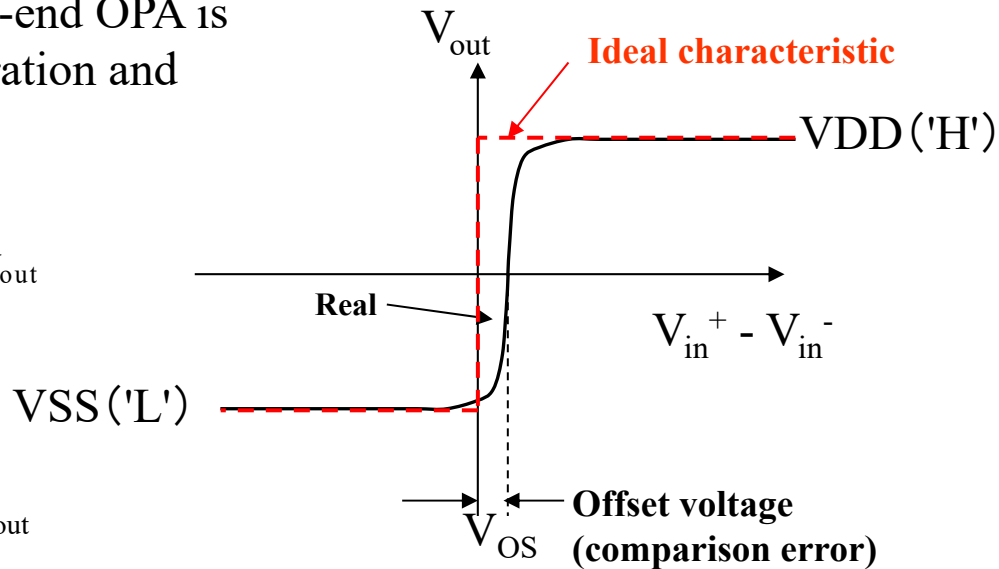
Function of analog comparator

- If ($V_{in}^+ > V_{in}^-$), then $V_{out} = VDD$ (Logic level = 'H')
- If ($V_{in}^+ < V_{in}^-$), then $V_{out} = VSS$ (Logic level = 'L')

The same symbol as a single-end OPA is used, but the circuit configuration and function is different.



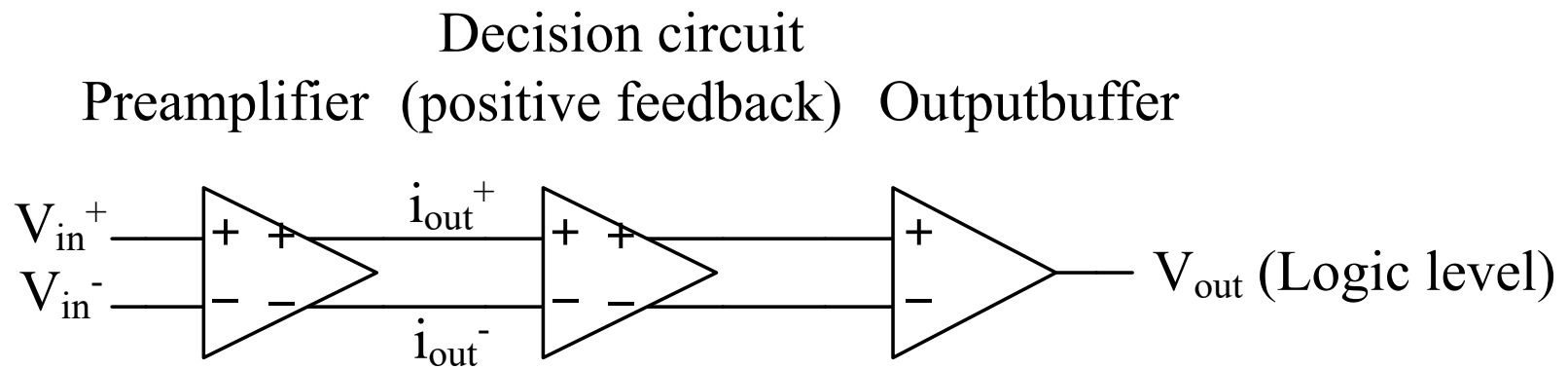
Symbol



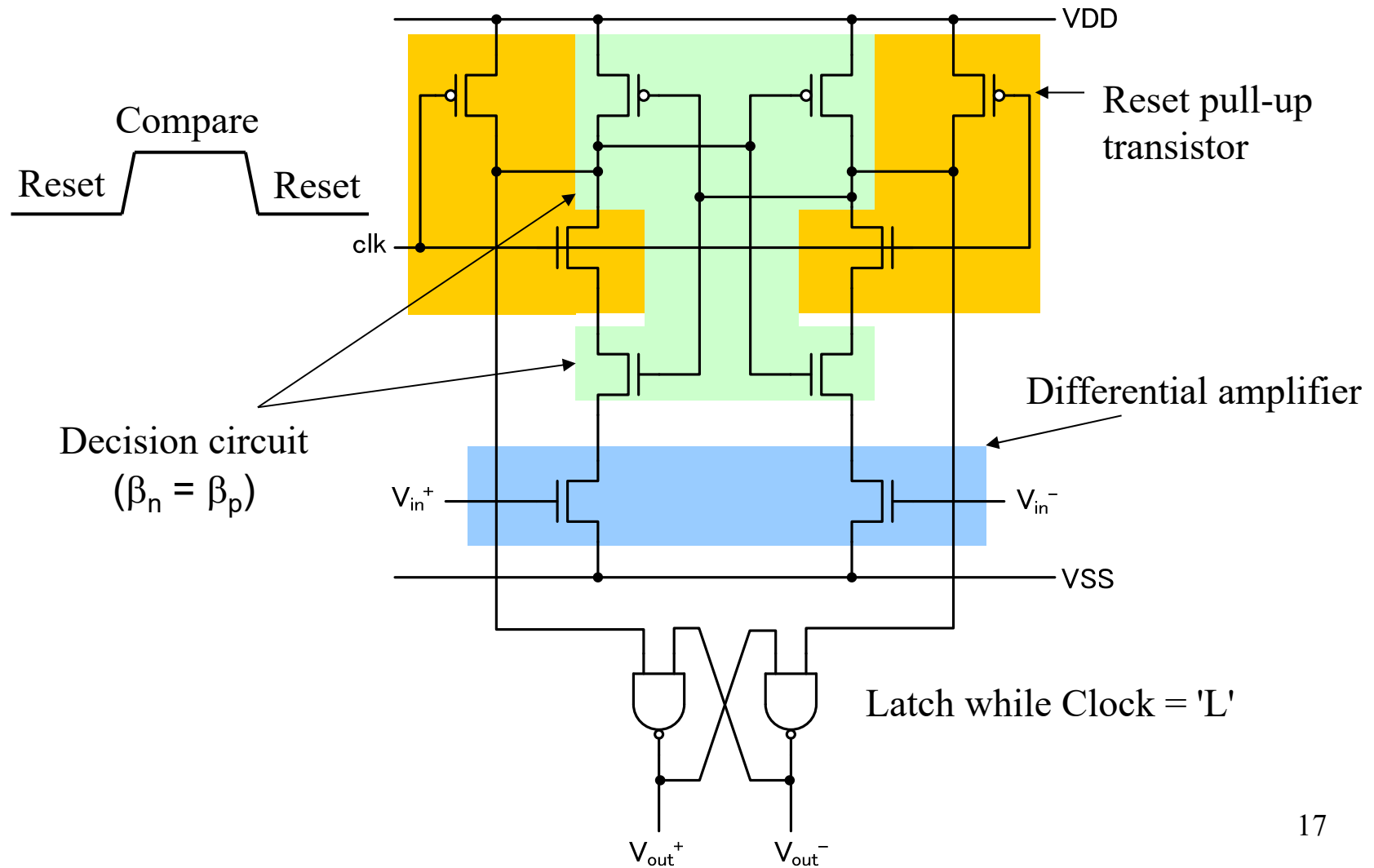
Specification of a comparator

Parameter	Design constraint	Description
VDD/VSS	max/typ/min	
I_{BIAS}	max	
I_{ACTIVE}	max	dependent on the clock frequency
f_S	typ	Clock frequency
Common-mode input range	min/max	
Input-referred offset V_{OS}	max	$V_{OS} \ll V_{LSB}/2$
Gain	min	Gain $\gg (VDD - VSS)/V_{LSB}$
Settling time	max	$\gg f_S$
Load capacitance	typ	

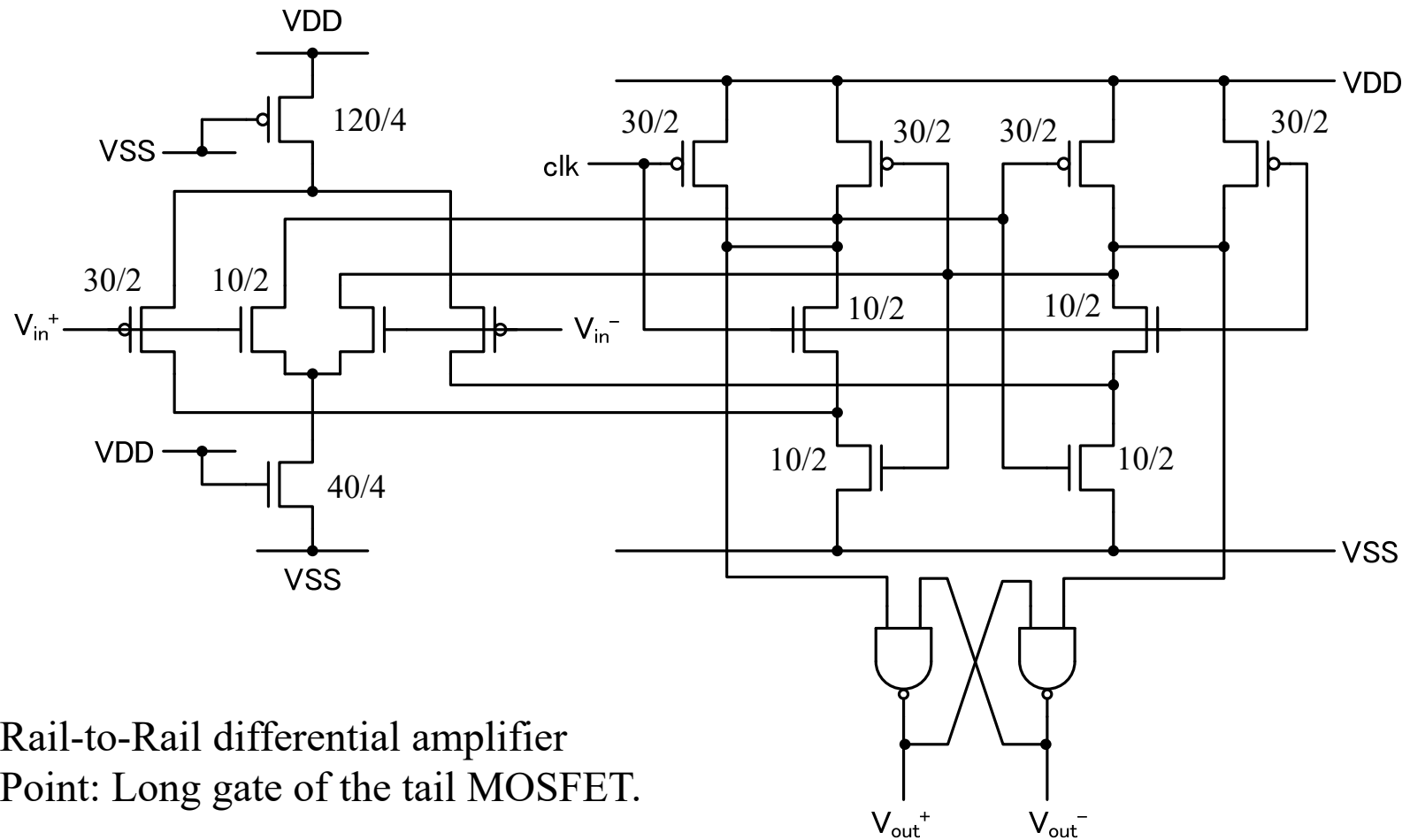
Block diagram of a comparator



Clocked Comparator (Sens. amp.)



Wide Swing Comparator

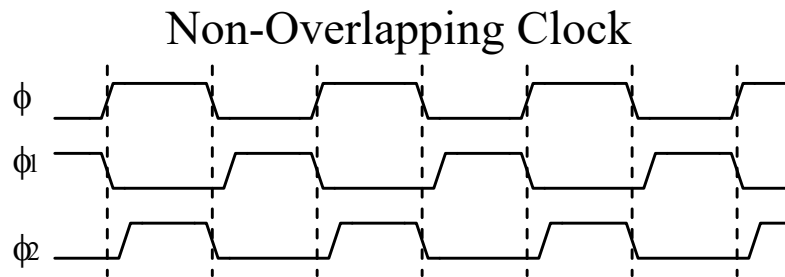


Rail-to-Rail differential amplifier
 Point: Long gate of the tail MOSFET.

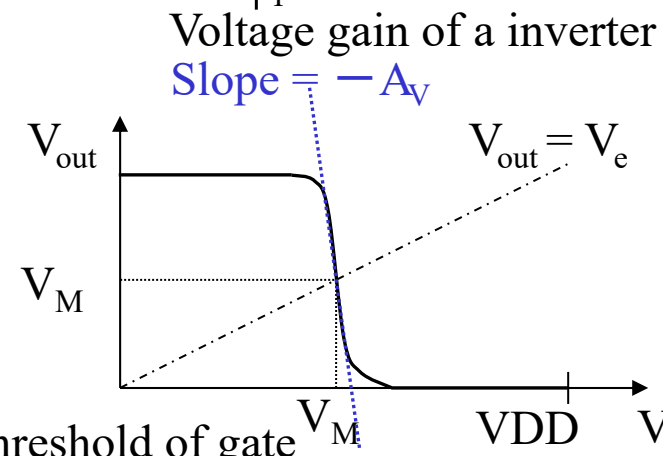
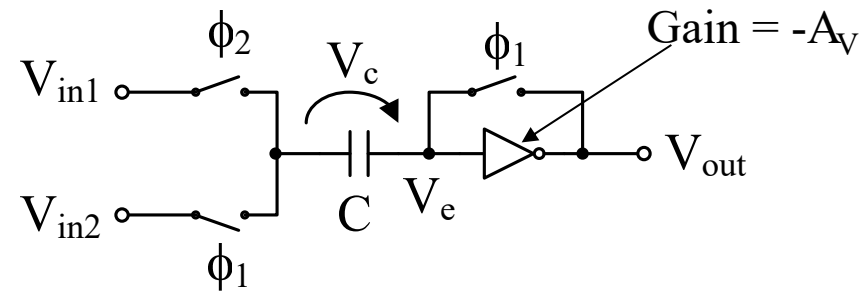
15.4 Dynamic comparator

Dynamic comparator

- Small area
- High precision (self-reference)
- Wide input range
- Cancelling noise and drift in lower frequency than the clock frequency

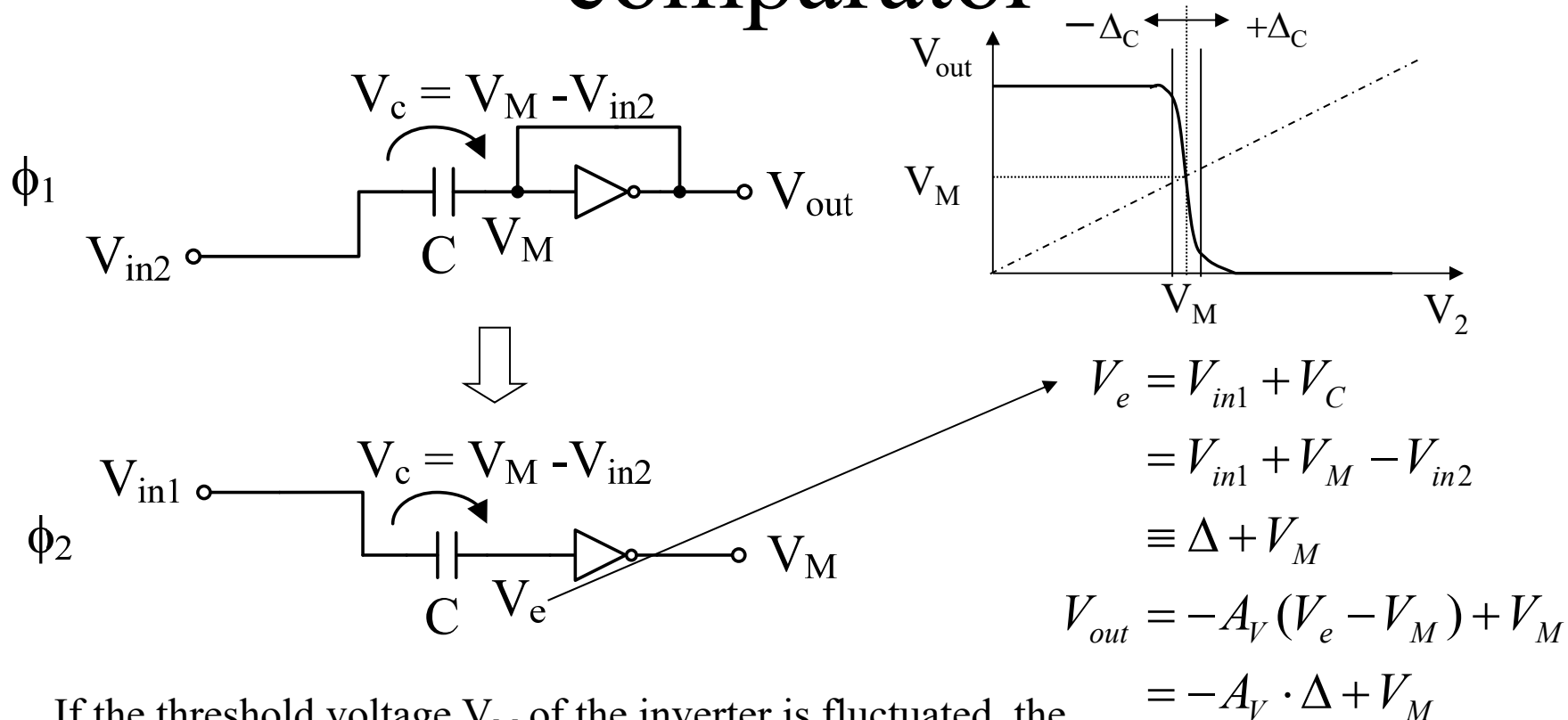


Clock phase	State
ϕ_1	Sample V_{in}^-
ϕ_2	Compare with V_{in}^+



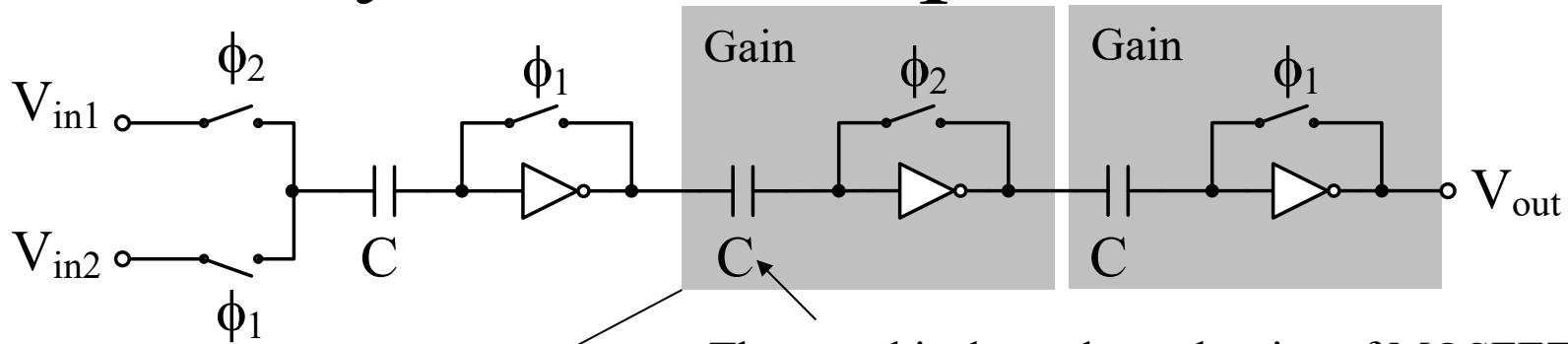
V_M : Threshold of gate

Operation of the dynamic comparator

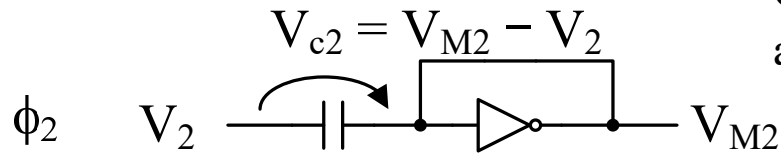


If the threshold voltage V_M of the inverter is fluctuated, the fluctuation of the offset voltage is negligible. Because only a comparison result Δ is amplified. The voltage gain of inverter A_V is normally low ($\sim 20\text{dB}$). The gain of the comparator can be increased by using additional inverter stage.

Practical implementation of the dynamic comparator



The speed is depends on the size of MOSFET and C, but the small capacitance suffers the kT/C noise and charge injection error of CMOS switch.



$$V_2 = -A_V \cdot \Delta + V_{M1}$$

$$V_{c2} = V_{M2} - V_2 = V_{M2} + A_V \cdot \Delta - V_{M1}$$

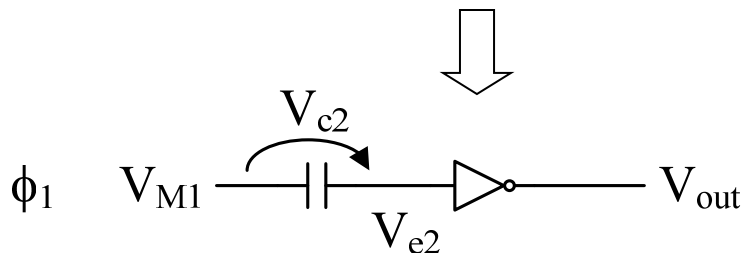
$$V_{e2} = V_{M1} + V_{c2} = V_{M1} + V_{M2} + A_V \cdot \Delta - V_{M1}$$

$$\equiv A_V \cdot \Delta + V_{M2}$$

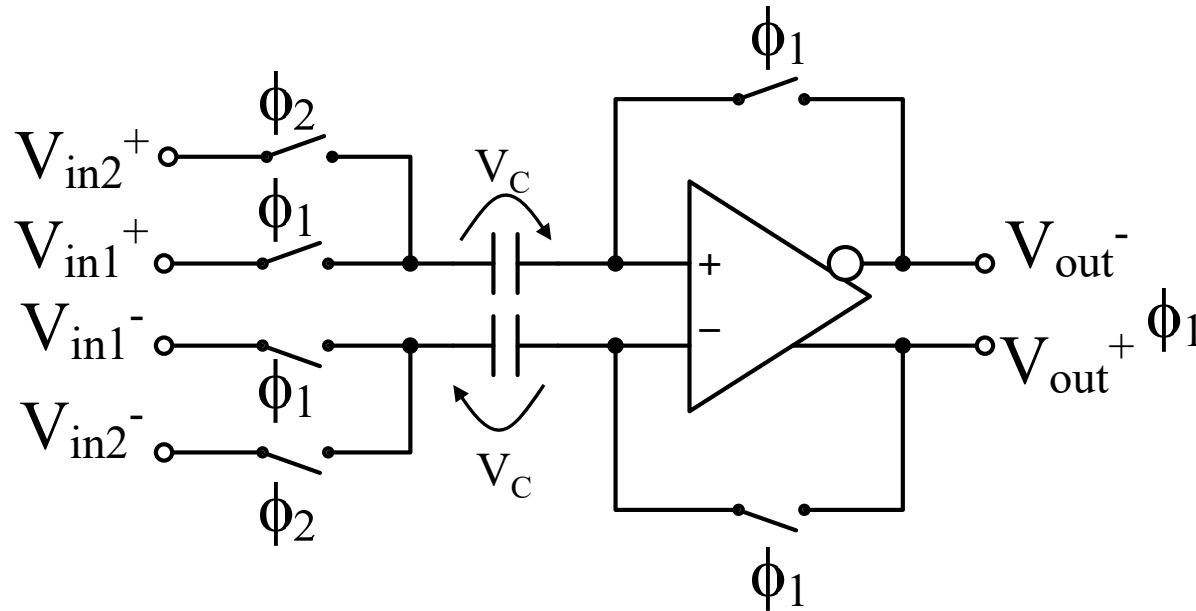
$$V_{out} = -A_V (V_{e2} - V_{M2})$$

$$= -A_V (A_V \cdot \Delta + V_{M2} - V_{M2}) + V_{M2}$$

$$= -A_V^2 \cdot \Delta + V_{M2}$$

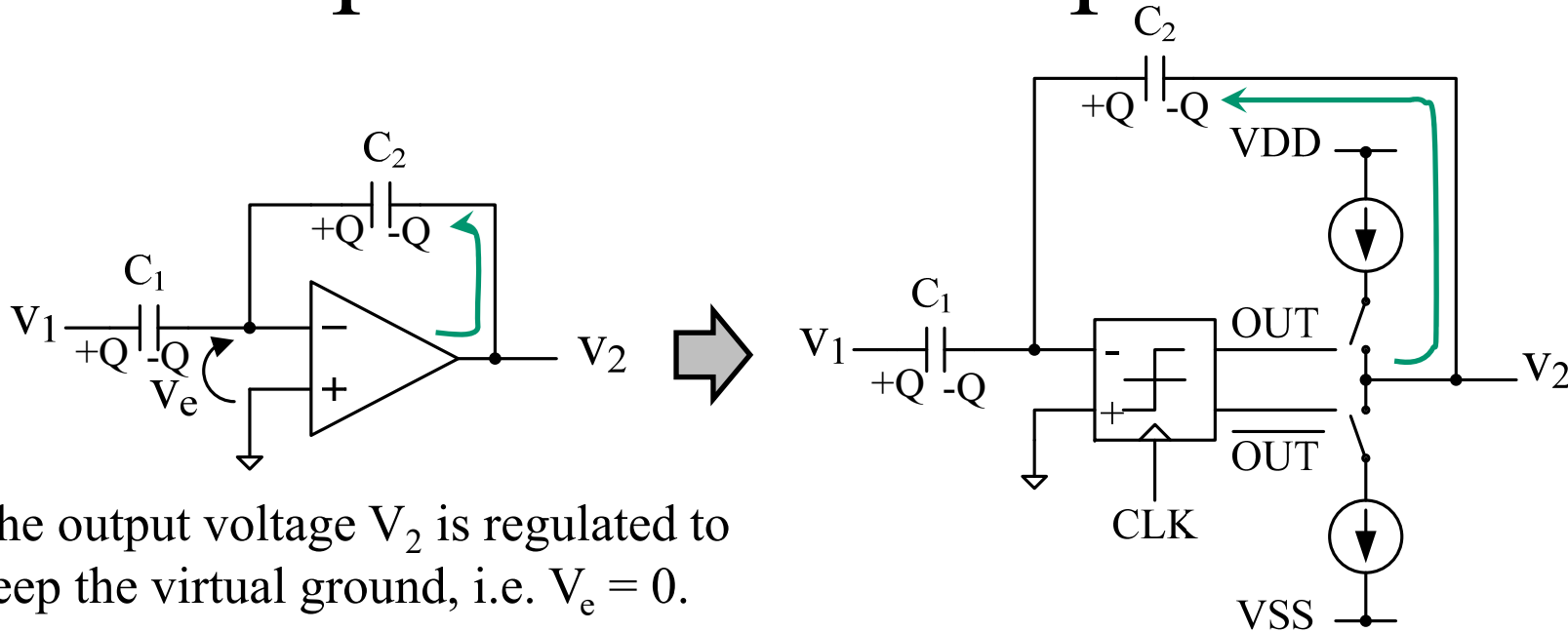


Full-differential dynamic comparator



Clock phase	State
ϕ_1	Sample V_1
ϕ_2	Compare with V_2

Discrete-time operational amplifier with comparator



The output voltage V_2 is regulated to keep the virtual ground, i.e. $V_e = 0$.

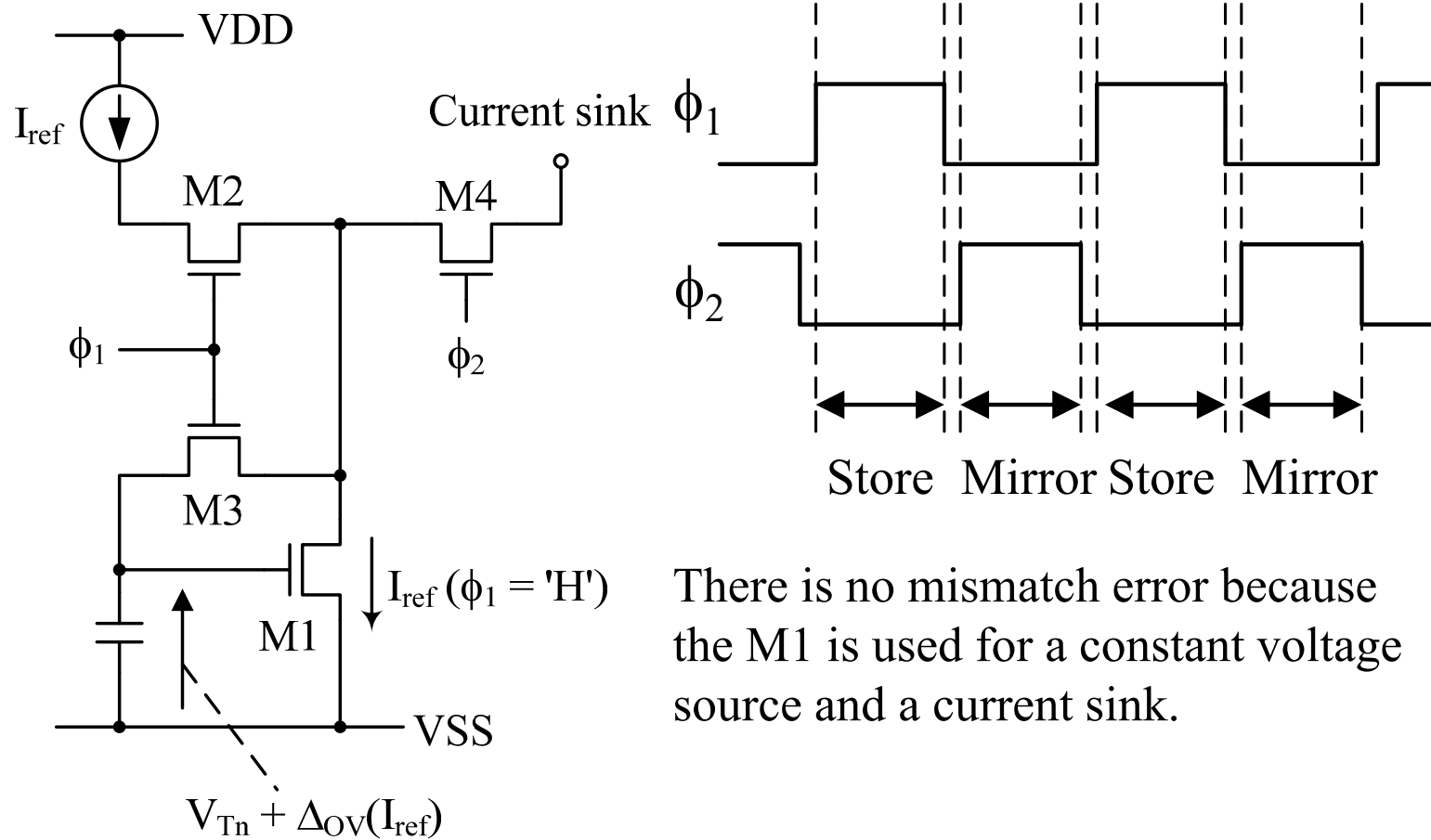
Equivalent circuit with comparator

The discrete time OPA can be replaced with high-precision comparator to implement the differential amplifier, because it is difficult to design the high gain OPA with the fine processes.

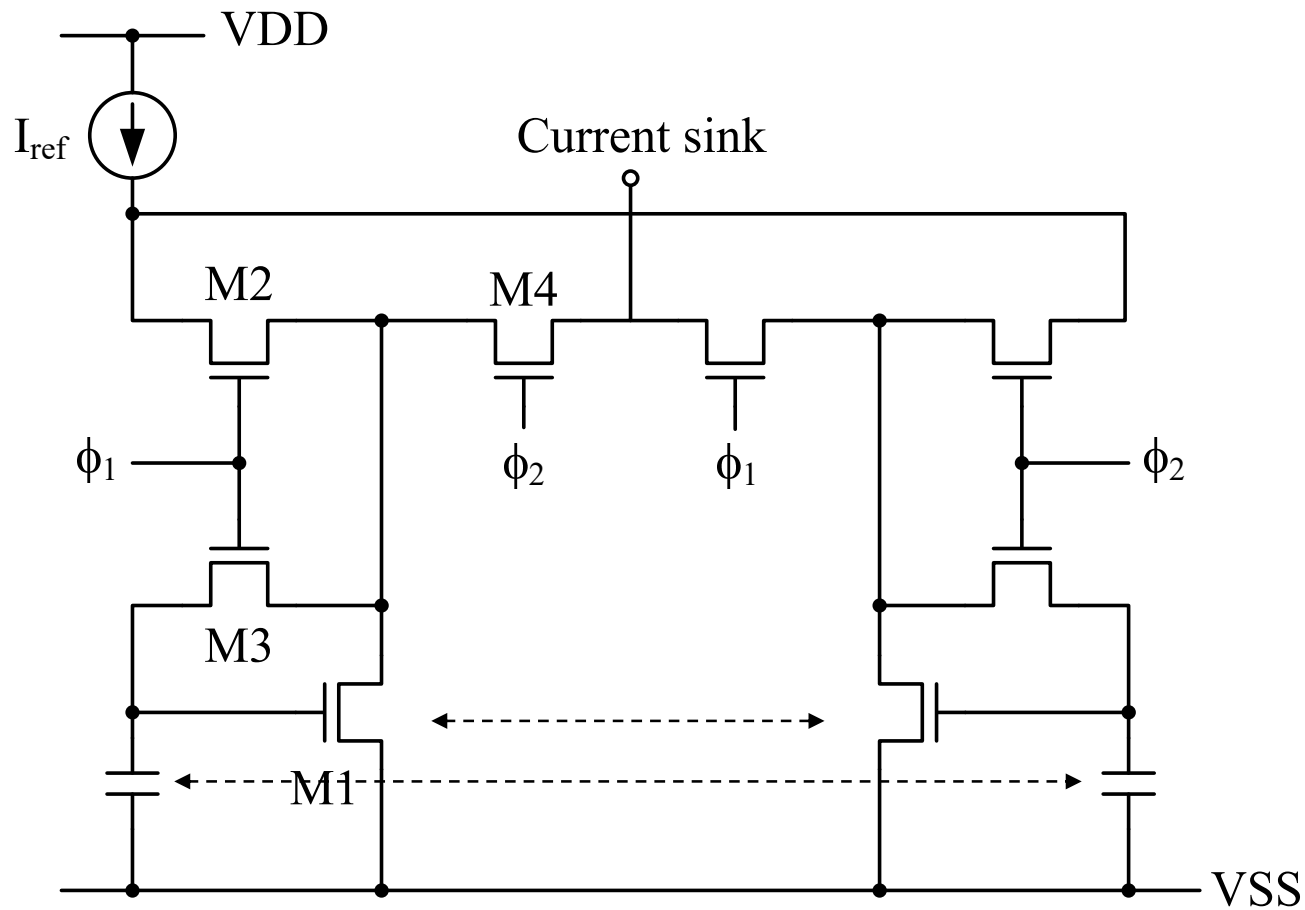
15.5 Dynamic amplifire

Dynamic analog circuits can avoid a mismatch error of MOSFET.

Discrete time dynamic current mirror

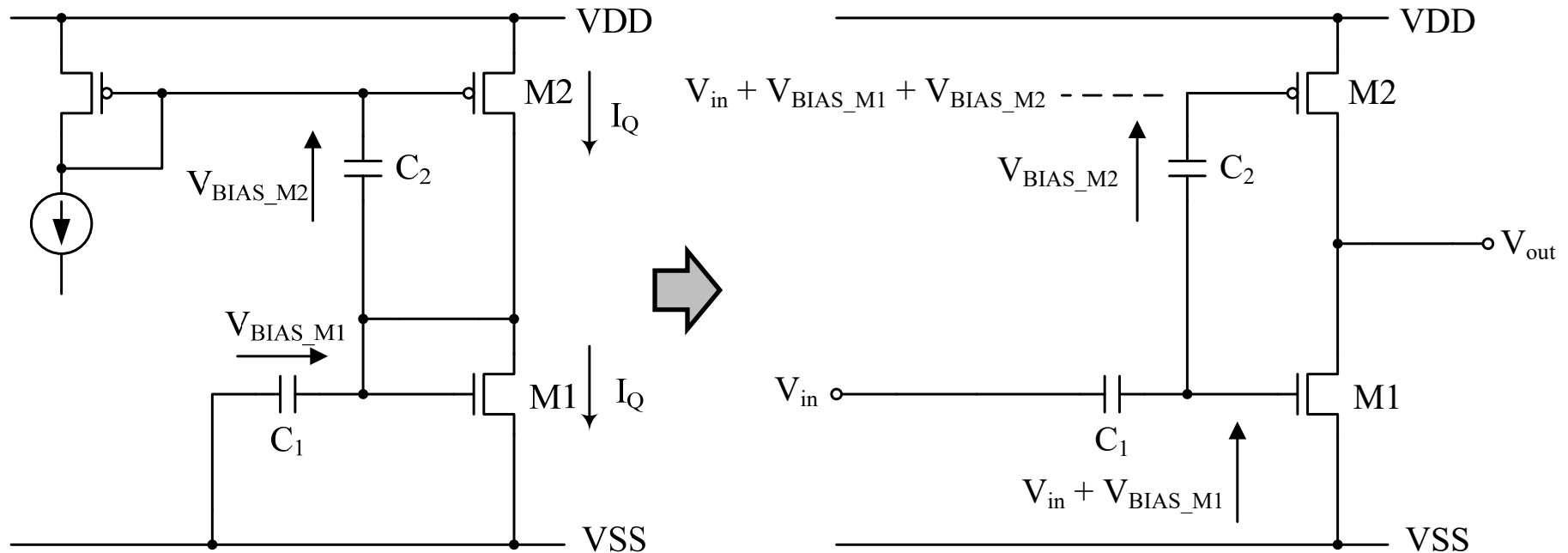


Continuous time dynamic current mirror



Matching of M1 and C are not required.

Dynamic class-AB amplifier



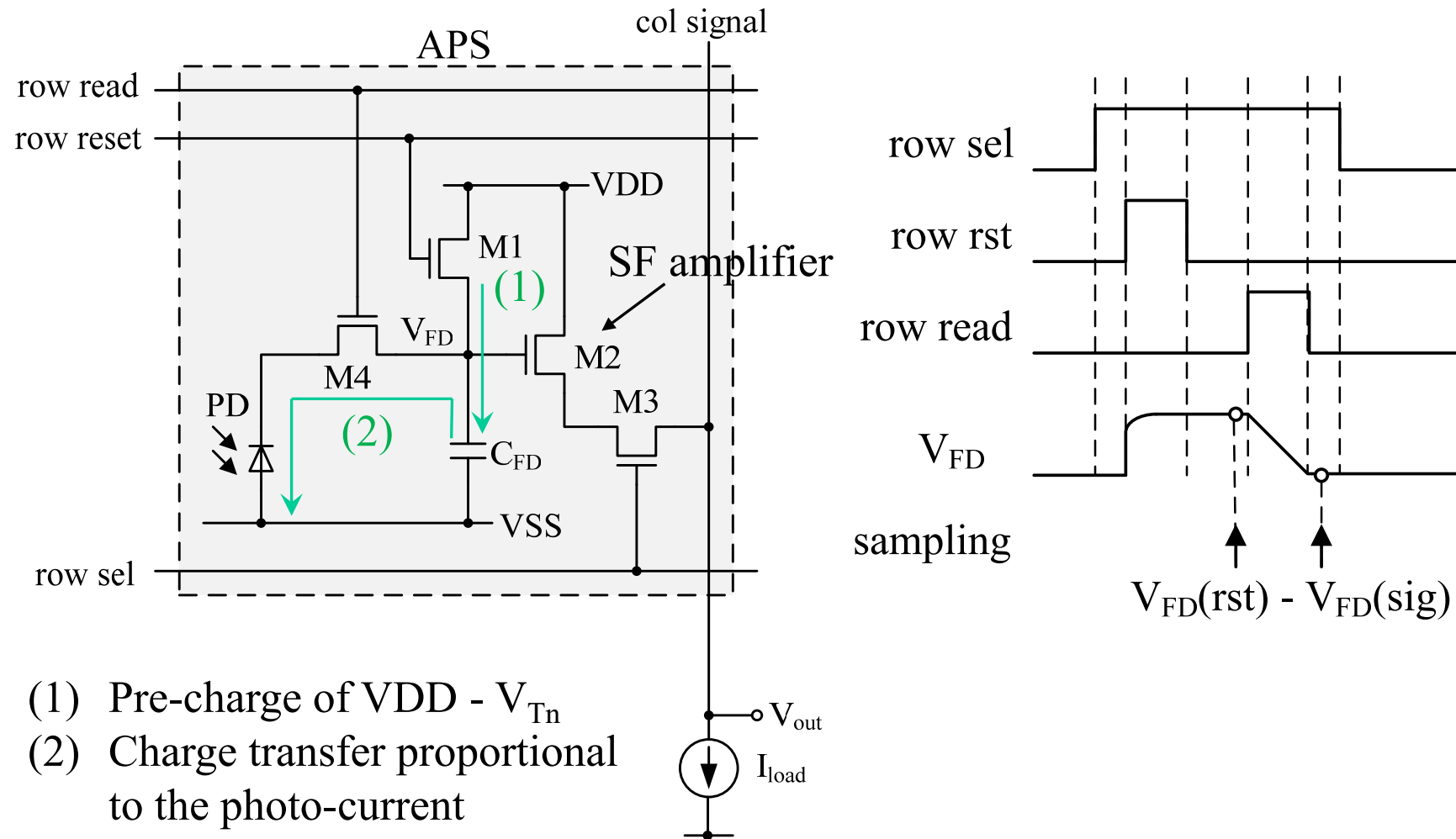
ϕ_1 : Storing phase of the bias condition for the quiescent current.

ϕ_2 : Amplification phase.

The biasing scheme makes the amplifier less sensitive to V_T and VDD variations.

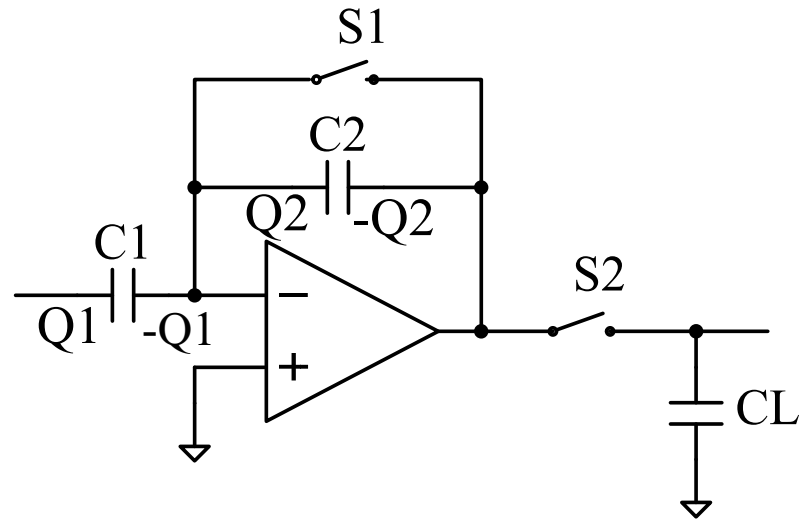
15.6 Active pixel sensor (APS)

4T active pixel sensor



Correlated double sampling

The fixed pattern noise (process variation) and switching noise are canceled by each correlated double sampling.



$$\begin{cases} S1 = \text{ON: } Q1 = C1V_{rst}, Q2 = 0 \\ S1 = \text{OFF: } Q1' = C1V_{sig}, Q2' = Q1 - Q1' \end{cases}$$

$$V_{out} = \frac{C1}{C2} (V_{sig} - V_{rst})$$

